

RoHS COMPLIANT

HALOGEN FREE

Available

Vishay Siliconix

P-Channel 12-V (D-S) MOSFET

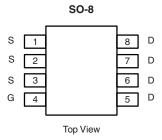
PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)			
	0.00825 at V _{GS} = - 4.5 V	- 14			
- 12	0.01025 at V _{GS} = - 2.5 V	- 13			
	0.013 at V _{GS} = - 1.8 V	- 12			

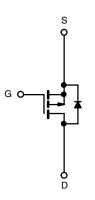
FEATURES

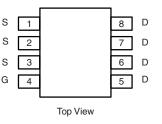
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

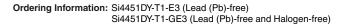
APPLICATIONS

- Load Switch
- Battery Switch









P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 12		V
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T _A = 25 °C	– I _D	- 14	- 10	
	T _A = 70 °C		- 11	- 8	
Pulsed Drain Current		I _{DM}	- 40		A
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 2.7	- 1.35	
	T _A = 25 °C	P	3.0	1.5	w
Maximum Power Dissipation ^a	T _A = 70 °C	P _D	1.9	0.95	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 t	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manimum has the Ambienta	t ≤ 10 s	R _{thJA}	33	42	
Maximum Junction-to-Ambient ^a	Steady State		70	85	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	17	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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Parameter	Symbol	Test Conditions		Тур.	Max.	Unit
Static			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -850 \ \mu A$	- 0.40		- 0.8	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V$, $V_{GS} = \pm 8 V$	= 0 V, V_{GS} = ± 8 V			nA
	I _{DSS}	$V_{DS} = -12 V, V_{GS} = 0 V$			- 1	
Zero Gate Voltage Drain Current		$V_{DS} = -12 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 70 ^{\circ}\text{C}$			- 5	μA
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -4.5 V$	- 30			Α
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -14 \text{ A}$		0.0065	0.00825	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 13 A		0.008	0.008 0.01025 0	
		V _{GS} = - 1.8 V, I _D = - 12 A 0.0105		0.013	1	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 14 A		55		S
Diode Forward Voltage ^a	V _{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.6	- 1.1	V
Dynamic ^b						
Total Gate Charge	Qg			81	120	
Gate-Source Charge	Q _{gs}	V_{DS} = - 6 V, V_{GS} = - 4.5 V, I_{D} = - 14 A		8.6		nC
Gate-Drain Charge	Q _{gd}			23.4		
Gate Resistance	R _g			3.0		Ω
Turn-On Delay Time	t _{d(on)}			55	85	
Rise Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		125	190	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		315	480	ns
Fall Time	t _f			235	360	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.7 A, dl/dt = 100 A/μs		185	300	

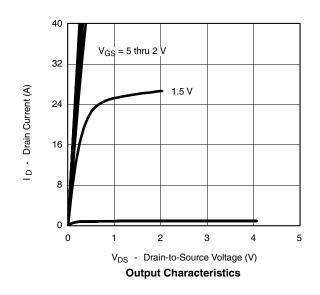
Notes:

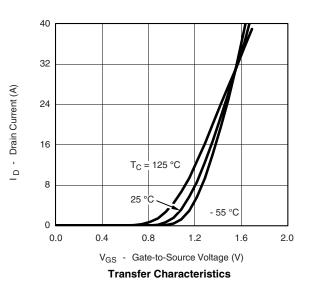
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Si4451DY Vishay Siliconix

C_{iss}

6

50

75

 $I_{D} = 14 \text{ A}$

100

125

150

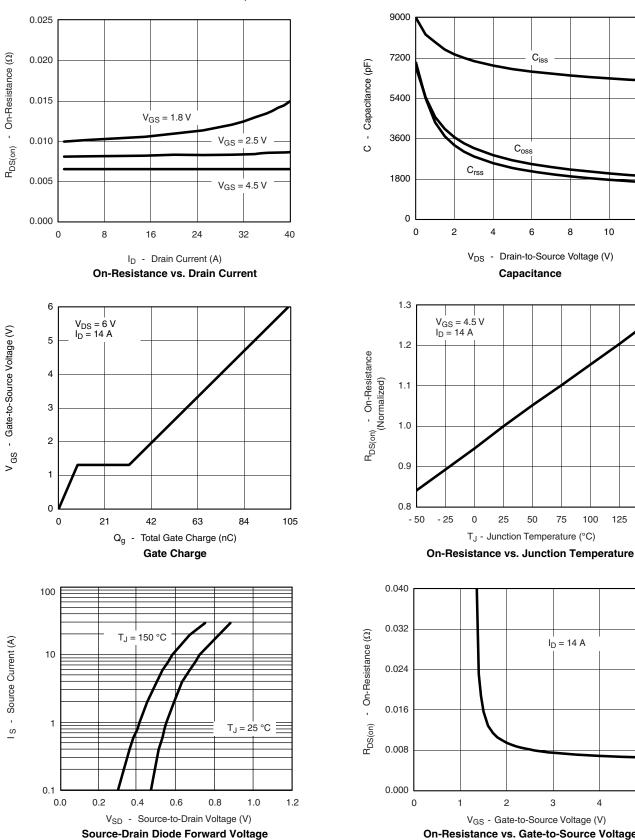
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10

12

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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On-Resistance vs. Gate-to-Source Voltage

3

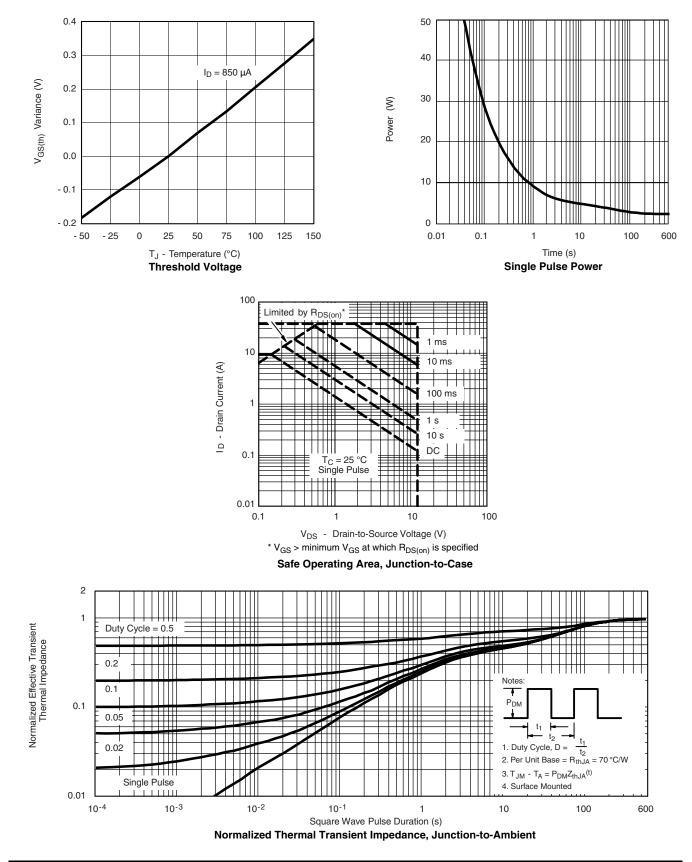
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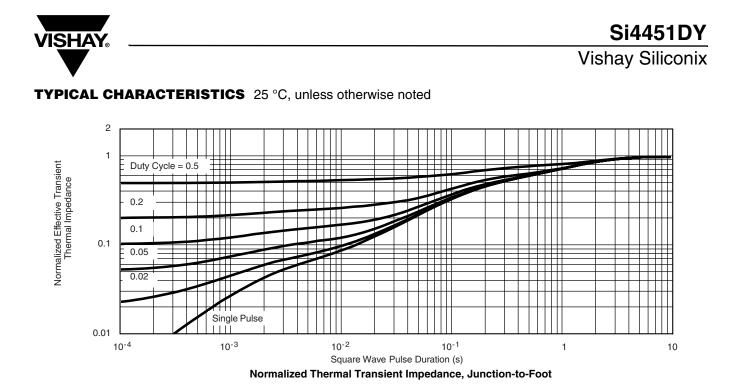
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg272115.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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